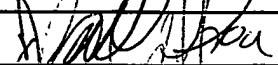


INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Complete if Known	
				Application Number	
				Filing Date	Concurrently Herewith
				First Named Inventor	Joseph J. Nahas
				Group Art Unit	
Examiner Name					
Sheet	1	of	1	Attorney Docket Number	
				SC13159TC	

U. S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number -Kind Code ² (if known)			
JS	AA	5,867,405	02/02/1999	Jiang <i>et al.</i>	
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		Country Code ³	Number ⁴ Kind Code ² (if known)				

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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JS	AN	U.S. Patent Application 10/302,203 filed November 22, 2002, entitled "Method and Apparatus for Simulating a Magnetoresistive Random Access Memory (MRAM)", assignee same as assignee hereof.	

Examiner Signature		Date Considered	12/12/05
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